

METHOD OF AND PLATEN FOR CONTROLLING REMOVAL RATE CHARACTERISTICS IN CHEMICAL MECHANICAL PLANARIZATION

5

ABSTRACT OF THE DISCLOSURE

Methods and a platen control parameters of a removal rate characteristic in chemical mechanical planarization, while allowing a low-cost polishing pad to be used especially in fast edge operations, and while reducing the amount of fluid used to support the polishing pad. Platen configuration provides fluid pressure control to reduce leakage
10 of fluid from beneath the polishing pad, and contributes to control of a location of an inflection point of the removal rate characteristic. Another configuration controls a shape of a section of the removal rate characteristic between the inflection point and a leading wafer edge.